Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of producing an oxide superconducting film ~~on a single-crystal substrate by~~ comprising:

depositing, on ~~the~~ a single-crystal substrate, substances scattered from a raw material due to irradiation with laser beams according to a pulsed-laser deposition method,

~~wherein~~ performing the irradiation of the raw material is ~~performed~~ in a manner such that the repetition frequency of the pulse irradiation of the laser beams is divided into at least two steps; a laser frequency of a second step being higher than the laser frequency of a first step and the laser frequency of the second step being less than 100 times the laser frequency of the first step.

2. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein the laser frequency of ~~a first step~~ the second step is not less than 2 times and not more than 40 times as high as the laser frequency of the first step in a case where the laser frequency of the first step is greater than or equal to 1 Hz and less than 20 HZ; and the laser frequency of the second step is not less than 2 times and not more than 5 times as high as the laser frequency of the first step in the case where the first laser frequency is 20 Hz. ~~smaller than the laser frequency of a second step.~~

3. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, ~~wherein the~~ further comprises providing the laser beam with a power ~~is~~ of greater than or equal to 400 mJ ~~or more~~.

4. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein ~~the~~ a temperature of the single-crystal substrate during the pulsed-laser deposition is more than or equal to 600°C and less than 1,200°C.

5. (Currently Amended) A method of producing an oxide superconducting film according to claim 3, wherein ~~the~~ a temperature of the single-crystal substrate during the pulsed-laser deposition is more than or equal to 600°C and less than 1,200°C.

6. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein ~~the~~ a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to ~~66.66~~100 Pa.

7. (Currently Amended) A method of producing an oxide superconducting film according to claim 6 [[3]], wherein ~~the~~ a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to ~~100~~ 66.66 Pa.

8. (Currently Amended) A method of producing an oxide superconducting film according to claim 4, wherein ~~the~~ a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to 100 Pa.

9. (Previously presented) A method of producing an oxide superconducting film according to claim 1, wherein the gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to 66.66 Pa.

10. (Currently Amended) A method of producing an oxide superconducting film according to claim 3, wherein ~~the~~ a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to 66.66 Pa.

11. (Currently Amended) A method of producing an oxide superconducting film according to claim 4, wherein ~~the~~ a gas pressure during the pulsed-laser deposition is within the range of 1.33 Pa to 66.66 Pa.

12. (Currently Amended) A method of producing an oxide superconducting film according to claim 1, wherein ~~the~~ an atmosphere during the pulsed-laser deposition contains oxygen.

13. (Currently Amended) A method of producing an oxide superconducting film according to claim 3, wherein ~~the~~ an atmosphere during the pulsed-laser deposition contains oxygen.

14. (Currently Amended) A method of producing an oxide superconducting film according to claim 4, wherein ~~the~~ a atmosphere during the pulsed-laser deposition contains oxygen.

15. (Currently Amended) A method of producing an oxide superconducting film according to claim 6, wherein ~~the~~ an atmosphere during the pulsed-laser deposition contains oxygen.

16. (Previously presented) A method of producing an oxide superconducting film according to claim 1, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.

17. (Previously presented) A method of producing an oxide superconducting film according to claim 3, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.

18. (Previously presented) A method of producing an oxide superconducting film according to claim 4, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.

19. (Previously presented) A method of producing an oxide superconducting film according to claim 6, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.

20. (Previously presented) A method of producing an oxide superconducting film according to claim 12, wherein the oxide superconducting film comprises an RE123 composition, where RE is composed of at least one of a rare-earth element and yttrium.